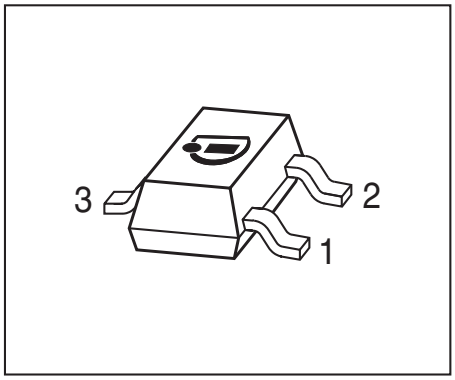
NPN Silicon High-Voltage Transistors



- Suitable for video output stages in TV sets and switching power supplies
- High breakdown voltage
- Low collector-emitter saturation voltage
- Complementary type: BFN27 (PNP)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101

AEC Qualified RoHS

Type	Marking	Pin Configuration			Package
BFN24	FHs	1=B	2=E	3=C	SOT23
BFN26	FJs	1=B	2=E	3=C	SOT23

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}		V
BFN24		250	
BFN26		300	
Collector-base voltage	V_{CBO}		
BFN24		250	
BFN26		300	
Emitter-base voltage	V_{EBO}	6	
Collector current	I_C	200	mA
Peak collector current, $t_p \leq 10$ ms	I_{CM}	500	
Base current	I_B	100	
Peak base current	I_{BM}	200	
Total power dissipation- $T_S \leq 74$ °C	P_{tot}	360	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[1)]	R_{thJS}	≤ 210	K/W

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	$V_{(BR)CEO}$				V
I_C = 1 mA, I_B = 0 , BFN24		250	-	-	
I_C = 1 mA, I_B = 0 , BFN26		300	-	-	
Collector-base breakdown voltage	$V_{(BR)CBO}$				
I_C = 100 µA, I_E = 0 , BFN24		250	-	-	
I_C = 100 µA, I_E = 0 , BFN26		300	-	-	
Emitter-base breakdown voltage	$V_{(BR)EBO}$	6	-	-	
I_E = 100 µA, I_C = 0					
Collector-base cutoff current	I_{CBO}				µA
V_{CB} = 200 V, I_E = 0 , BFN24		-	-	0.1	
V_{CB} = 250 V, I_E = 0 , BFN26		-	-	0.1	
V_{CB} = 200 V, I_E = 0 , T_A = 150 °C, BFN24		-	-	20	
V_{CB} = 250 V, I_E = 0 , T_A = 150 °C, BFN26		-	-	20	
Emitter-base cutoff current	I_{EBO}	-	-	100	nA
V_{EB} = 5 V, I_C = 0					
DC current gain[2)]	h_{FE}				-
I_C = 1 mA, V_{CE} = 10 V		25	-	-	
I_C = 10 mA, V_{CE} = 10 V		40	-	-	
I_C = 30 mA, V_{CE} = 10 V, BFN24		40	-	-	
I_C = 30 mA, V_{CE} = 10 V, BFN26		30	-	-	
Collector-emitter saturation voltage[2)]	V_{CEsat}				V
I_C = 20 mA, I_B = 2 mA, BFN24		-	-	0.4	
I_C = 20 mA, I_B = 2 mA, BFN26		-	-	0.5	
Base emitter saturation voltage[2)]	V_{BEsat}	-	-	0.9	
I_C = 20 mA, I_B = 2 mA					

[1]For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

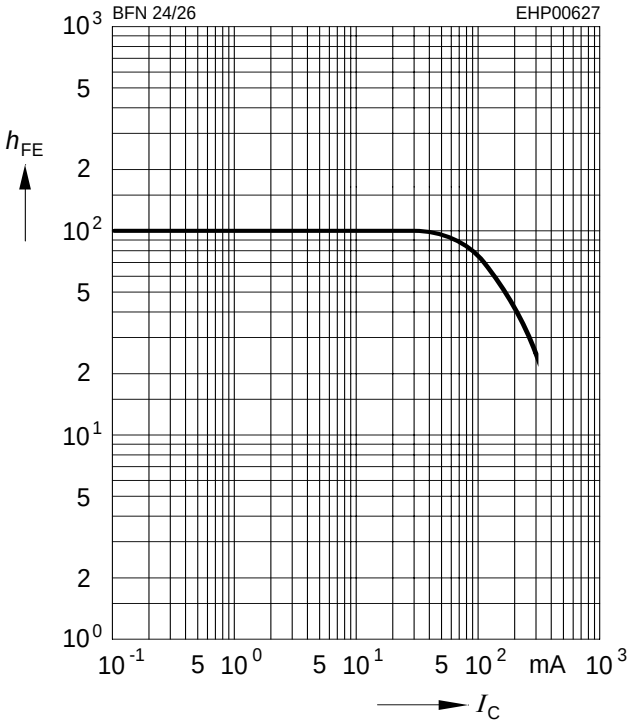
[2]Pulse test: t < 300µs; D < 2%

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Transition frequency I_C = 20 mA, V_{CE} = 10 V, f = 20 MHz	f_T	-	70	-	MHz
Collector-base capacitance V_{CB} = 30 V, f = 1 MHz	C_{cb}	-	1.5	-	pF

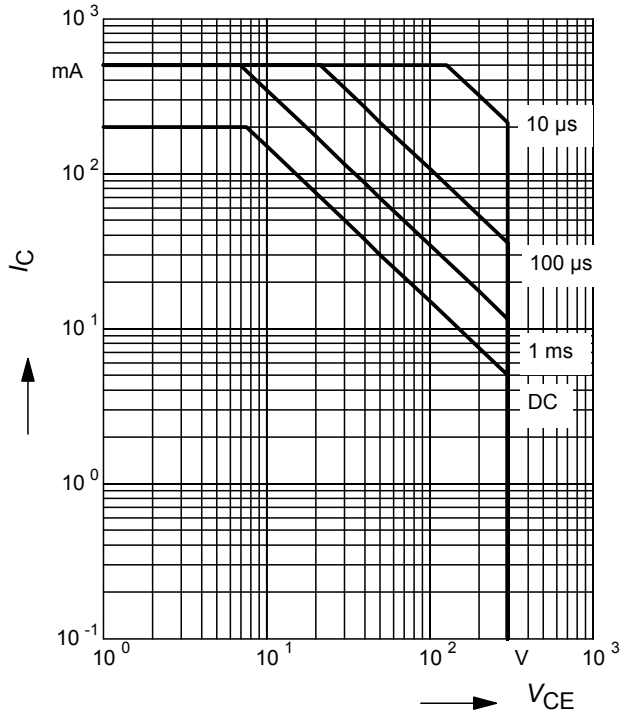
DC current gain $h_{FE} = f(I_C)$

V_{CE} = 10 V



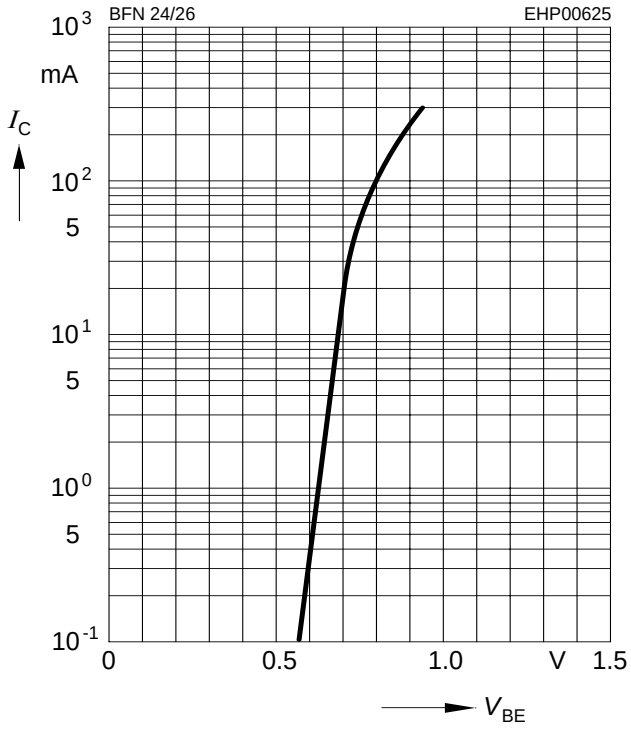
Operating range $I_C = f(V_{CEO})$

T_A = 25°C, D = 0



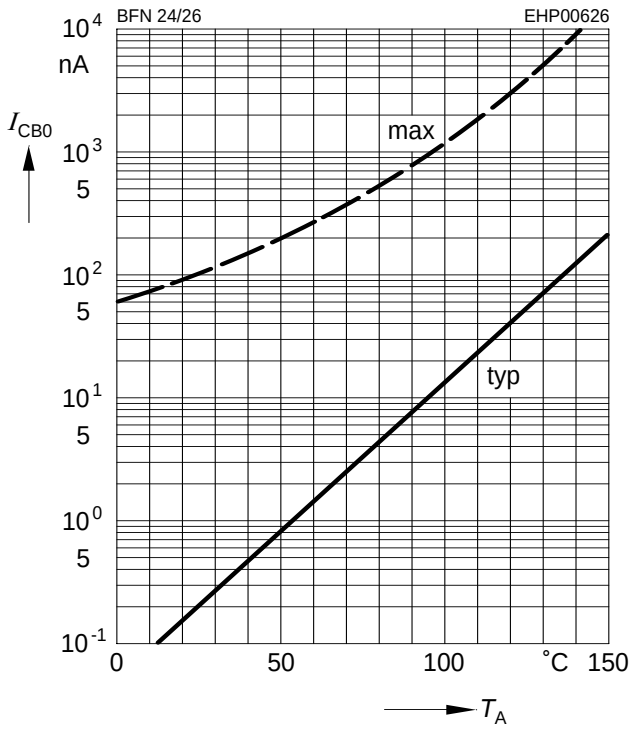
Collector current $I_C = f(V_{BE})$

V_{CE} = 10 V

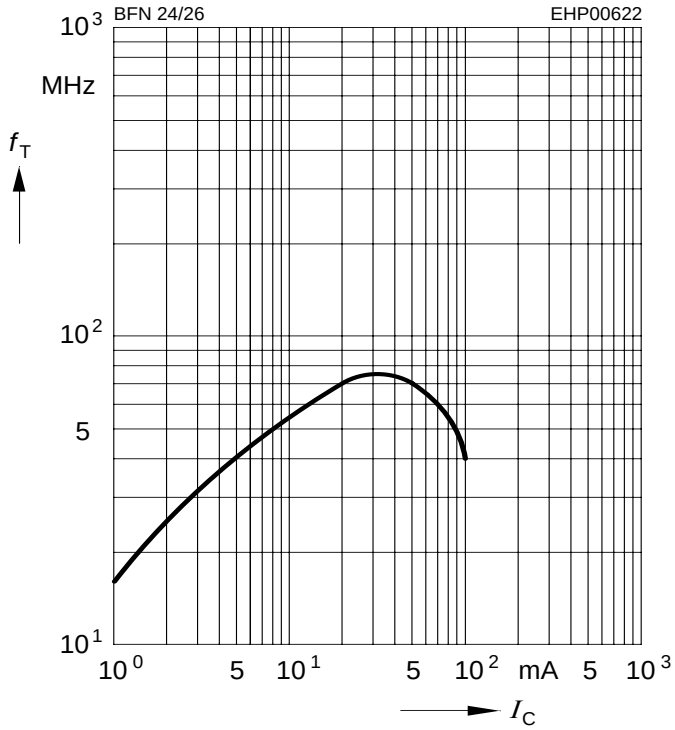


Collector cutoff current $I_{CBO} = f(T_A)$

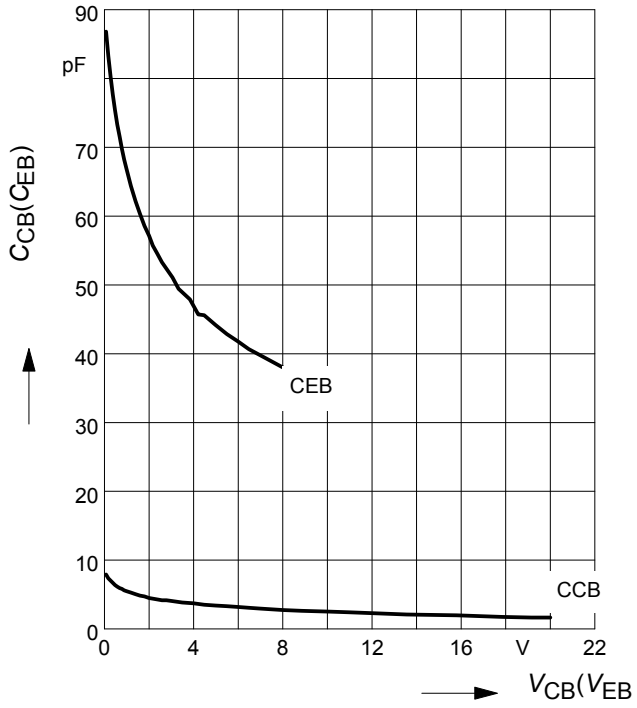
V_{CB} = 200 V



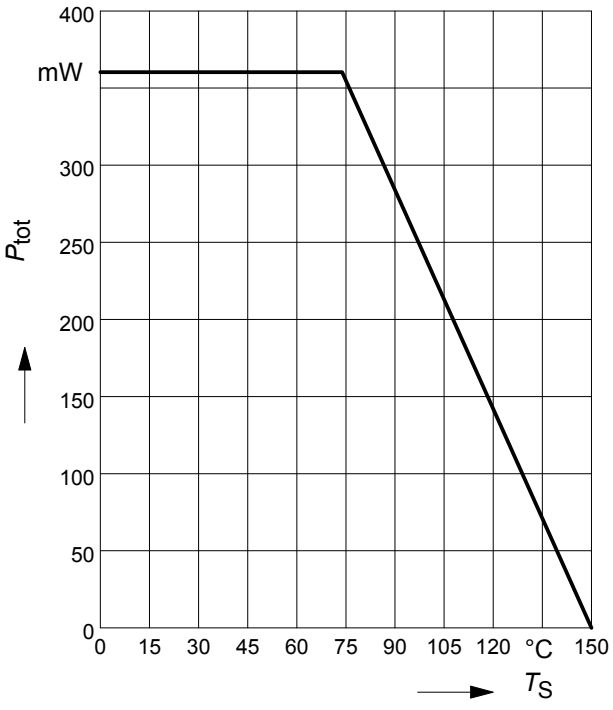
Transition frequency $f_T = f(I_C)$
V_{CE} = parameter in V, f = 2 GHz



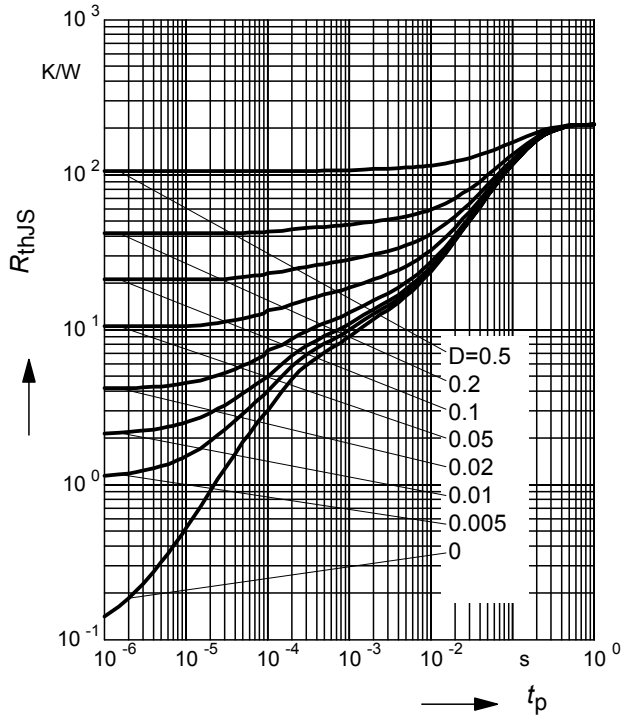
Collector-base capacitance $C_{cb} = f(V_{CB})$
Emitter-base capacitance $C_{eb} = f(V_{EB})$



Total power dissipation $P_{tot} = f(T_S)$

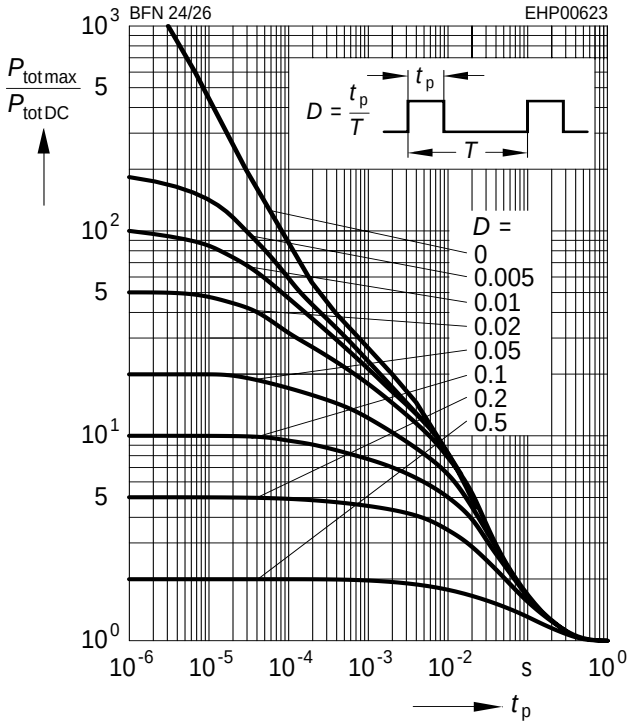


Permissible Pulse Load $R_{thJS} = f(t_p)$

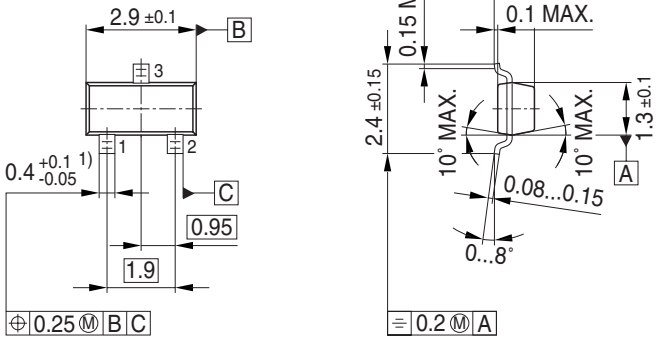


Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

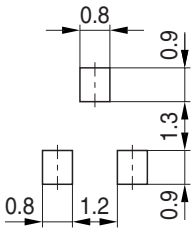


Package Outline

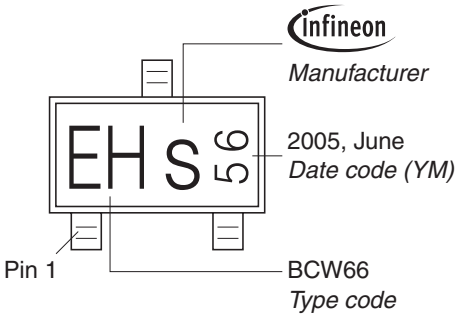


1) Lead width can be 0.6 max. in dambar area

Foot Print

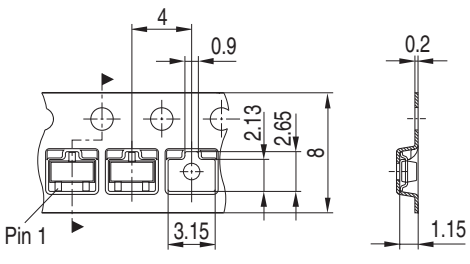


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



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